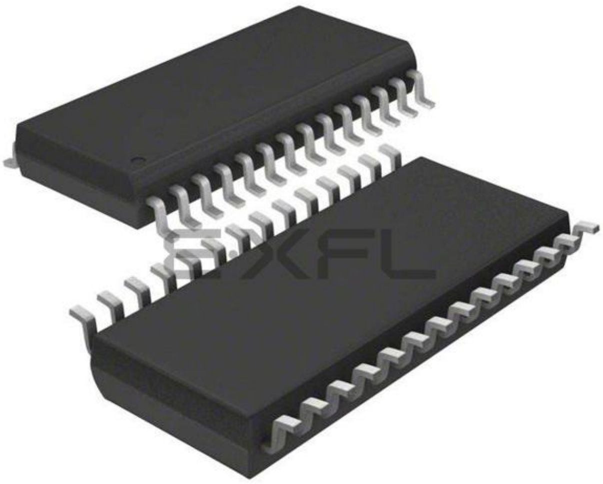

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	24MHz
Connectivity	I²C, IrDA, LINbus, Microwire, SmartCard, SPI, SSP, UART/USART
Peripherals	Brown-out Detect/Reset, CapSense, LCD, LVD, POR, PWM, WDT
Number of I/O	24
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 5.5V
Data Converters	A/D 8x12b SAR; D/A 2xIDAC
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	28-SSOP (0.209", 5.30mm Width)
Supplier Device Package	28-SSOP
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/cy8c4125pva-482t

Functional Overview

CPU and Memory Subsystem

CPU

The Cortex-M0 CPU in PSoC 4100 is part of the 32-bit MCU subsystem, which is optimized for low power operation with extensive clock gating. It mostly uses 16-bit instructions and executes a subset of the Thumb-2 instruction set. This enables fully compatible binary upward migration of the code to higher performance processors such as the Cortex-M3 and M4, thus enabling upward compatibility. The Cypress implementation includes a hardware multiplier that provides a 32-bit result in one cycle. It includes a nested vectored interrupt controller (NVIC) block with 32 interrupt inputs and also includes a Wakeup Interrupt Controller (WIC), which can wake the processor up from Deep Sleep mode allowing power to be switched off to the main processor when the chip is in Deep Sleep mode. The Cortex-M0 CPU provides a Non-Maskable Interrupt input (NMI), which is made available to the user when it is not in use for system functions requested by the user.

The CPU also includes a debug interface, the Serial Wire Debug (SWD) interface, which is a 2-wire form of JTAG; the debug configuration used for PSoC 4100 has four break-point (address) comparators and two watchpoint (data) comparators.

Flash

PSoC 4100 has a flash module with a flash accelerator tightly coupled to the CPU to improve average access times from the flash block. The flash block is designed to deliver 0 wait-state (WS) access time at 24 MHz. Part of the flash module can be used to emulate EEPROM operation if required.

The PSoC 4100 flash supports the following flash protection modes at the memory sub-system level.

Open: No protection. Factory default mode that the product is shipped in.

Protected: User may change from Open to Protected. This mode disables debug interface accesses. The mode can be set back to Open but only after completely erasing the flash.

Kill: User may change from Open to Kill. This mode disables all debug accesses. The part cannot be erased externally, thus obviating the possibility of partial erasure by power interruption and potential malfunction and security leaks. This is an irrecvocable mode.

In addition, row-level Read/Write protection is also supported to prevent inadvertent Writes as well as selectively block Reads. Flash Read/Write/Erase operations are always available for internal code using system calls.

SRAM

SRAM memory is retained during Hibernate.

SROM

A supervisory ROM that contains boot and configuration routines is provided.

System Resources

Power System

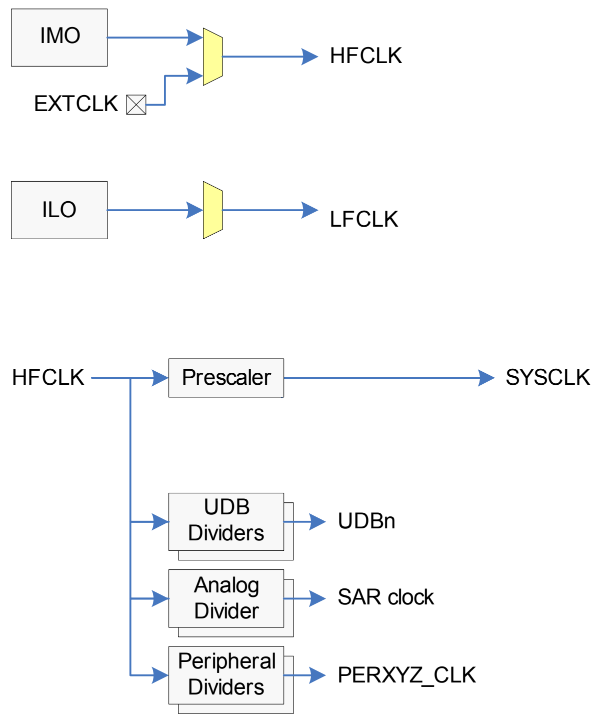
The power system is described in detail in the section Power on page 10. It provides assurance that voltage levels are as required for each respective mode and either delay mode entry (on power-on reset (POR), for example) until voltage levels are as required for proper function or generate resets (brown-out detect (BOD)) or interrupts (low-voltage detect (LVD)). The PSoC 4100 operates with a single external supply over the range of 1.71 V to 5.5 V and has five different power modes, transitions between which are managed by the power system. The PSoC 4100 provides Sleep, Deep Sleep, Hibernate, and Stop low-power modes.

Clock System

The PSoC 4100 clock system is responsible for providing clocks to all subsystems that require clocks and for switching between different clock sources without glitching. In addition, the clock system ensures that no metastable conditions occur.

The clock system for the PSoC 4100 consists of two internal oscillators, IMO and the ILO, and provision for an external clock.

Figure 1. PSoC 4100 MCU Clocking Architecture



The HFCLK signal can be divided down (see PSoC 4100 MCU Clocking Architecture) to generate synchronous clocks for the analog and digital peripherals. There are a total of 12 clock dividers for the PSoC 4100, each with 16-bit divide capability. The analog clock leads the digital clocks to allow analog events to occur before digital clock-related noise is generated. The 16-bit capability allows a lot of flexibility in generating fine-grained frequency values and is fully supported in PSoC Creator.

IMO Clock Source

The IMO is the primary source of internal clocking in the PSoC 4100. It is trimmed during testing to achieve the specified accuracy. Trim values are stored in nonvolatile latches (NVL). Additional trim settings from flash can be used to compensate for changes. The IMO default frequency is 24 MHz and it can be adjusted between 3 MHz to 24 MHz in steps of 1 MHz. IMO tolerance with Cypress-provided calibration settings is ±2%.

ILO Clock Source

The ILO is a very low power oscillator, which is primarily used to generate clocks for peripheral operation in Deep Sleep mode. ILO-driven counters can be calibrated to the IMO to improve accuracy. Cypress provides a software component, which does the calibration.

Watchdog Timer

A watchdog timer is implemented in the clock block running from the ILO; this allows watchdog operation during Deep Sleep and generates a watchdog reset if not serviced before the timeout occurs. The watchdog reset is recorded in the Reset Cause register.

Reset

PSoC 4100 can be reset from a variety of sources including a software reset. Reset events are asynchronous and guarantee reversion to a known state. The reset cause is recorded in a register, which is sticky through reset and allows software to determine the cause of the Reset. An XRES pin is reserved for external reset to avoid complications with configuration and multiple pin functions during power-on or reconfiguration. The XRES pin has an internal pull-up resistor that is always enabled.

Voltage Reference

The PSoC 4100 reference system generates all internally required references. A 1% voltage reference spec is provided for the 12-bit ADC. To allow better signal-to-noise ratios (SNR) and better absolute accuracy, it is possible to bypass the internal reference using a GPIO pin or to use an external reference for the SAR.

Analog Blocks

12-bit SAR ADC

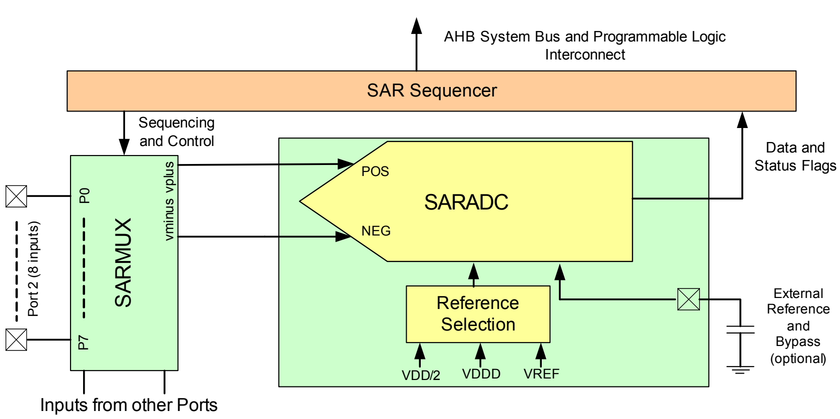
The 12-bit 806 Ksps SAR ADC can operate at a maximum clock rate of 14.5 MHz and requires a minimum of 18 clocks at that frequency to do a 12-bit conversion.

The block functionality is augmented for the user by adding a reference buffer to it (trimmable to ±1%) and by providing the choice (for the PSoC 4100 case) of three internal voltage references: V_{DD}, $V_{DD}/2$, and V_{REF} (nominally 1.024 V) as well as an external reference through a GPIO pin. The Sample-and-Hold (S/H) aperture is programmable allowing the gain bandwidth requirements of the amplifier driving the SAR inputs, which determine its settling time, to be relaxed if required. System performance will be 65 dB for true 12-bit precision providing appropriate references are used and system noise levels permit. To improve performance in noisy conditions, it is possible to provide an external bypass (through a fixed pin location) for the internal reference amplifier.

The SAR is connected to a fixed set of pins through an 8-input sequencer. The sequencer cycles through selected channels autonomously (sequencer scan) and does so with zero switching overhead (that is, aggregate sampling bandwidth is equal to 806 Ksps whether it is for a single channel or distributed over several channels). The sequencer switching is effected through a state machine or through firmware-driven switching. A feature provided by the sequencer is buffering of each channel to reduce CPU interrupt service requirements. To accommodate signals with varying source impedance and frequency, it is possible to have different sample times programmable for each channel. Also, signal range specification through a pair of range registers (low and high range values) is implemented with a corresponding out-of-range interrupt if the digitized value exceeds the programmed range; this allows fast detection of out-of-range values without the necessity of having to wait for a sequencer scan to be completed and the CPU to read the values and check for out-of-range values in software.

The SAR is able to digitize the output of the on-board temperature sensor for calibration and other temperature-dependent functions. The SAR is not available in Deep Sleep and Hibernate modes as it requires a high-speed clock (up to 18 MHz). The SAR operating range is 1.71 V to 5.5 V.

Figure 2. SAR ADC System Diagram



GPIO

PSoC 4100 has 24 GPIOs. The GPIO block implements the following:

- Eight drive strength modes:
  - Analog input mode (input and output buffers disabled)
  - Input only
  - Weak pull-up with strong pull-down
  - Strong pull-up with weak pull-down
  - Open drain with strong pull-down
  - Open drain with strong pull-up
  - Strong pull-up with strong pull-down
  - Weak pull-up with weak pull-down
- Input threshold select (CMOS or LVTTL).
- Individual control of input and output buffer enabling/disabling in addition to the drive strength modes.
- Hold mode for latching previous state (used for retaining I/O state in Deep Sleep mode and Hibernate modes).
- Selectable slew rates for dV/dt related noise control to improve EMI.

The pins are organized in logical entities called ports, which are 8-bit in width. During power-on and reset, the blocks are forced to the disable state so as not to crowbar any inputs and/or cause excess turn-on current. A multiplexing network known as a high-speed I/O matrix is used to multiplex between various signals that may connect to an I/O pin. Pin locations for fixed-function peripherals are also fixed to reduce internal multiplexing complexity.

Data output and pin state registers store, respectively, the values to be driven on the pins and the states of the pins themselves.

Every I/O pin can generate an interrupt if so enabled and each I/O port has an interrupt request (IRQ) and interrupt service routine (ISR) vector associated with it (5 for PSoC 4100).

Special Function Peripherals

LCD Segment Drive

The PSoC 4100 has an LCD controller which can drive up to four commons and up to 32 segments. It uses full digital methods to drive the LCD segments requiring no generation of internal LCD voltages. The two methods used are referred to as digital correlation and PWM.

Digital correlation pertains to modulating the frequency and levels of the common and segment signals to generate the highest RMS voltage across a segment to light it up or to keep the RMS signal zero. This method is good for STN displays but may result in reduced contrast with TN (cheaper) displays.

PWM pertains to driving the panel with PWM signals to effectively use the capacitance of the panel to provide the integration of the modulated pulse-width to generate the desired LCD voltage. This method results in higher power consumption but can result in better results when driving TN displays. LCD operation is supported during Deep Sleep refreshing a small display buffer (4 bits; 1 32-bit register per port).

CapSense

CapSense is supported on all pins in the PSoC 4100 through a CapSense Sigma-Delta (CSD) block that can be connected to any pin through an analog mux bus that any GPIO pin can be connected to via an Analog switch. CapSense function can thus be provided on any pin or group of pins in a system under software control. A component is provided for the CapSense block to make it easy for the user.

Shield voltage can be driven on another Mux Bus to provide water tolerance capability. Water tolerance is provided by driving the shield electrode in phase with the sense electrode to keep the shield capacitance from attenuating the sensed input.

The CapSense block has two IDACs which can be used for general purposes if CapSense is not being used.(both IDACs are available in that case) or if CapSense is used without water tolerance (one IDAC is available).

VDDA: Analog V_{DD} pin where package pins allow; shorted to V_{DDD} otherwise.

VSSA: Analog ground pin where package pins allow; shorted to VSS otherwise

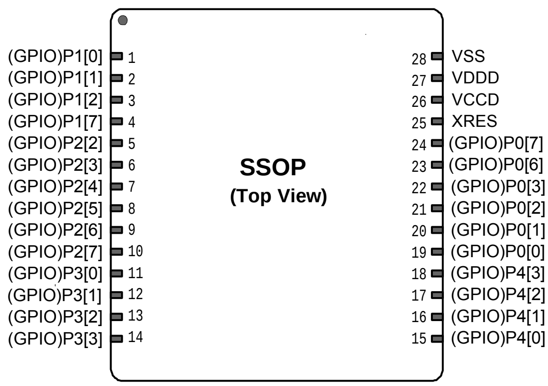
VSS: Ground pin.

VCCD: Regulated Digital supply (1.8 V ±5%).

Port Pins can all be used as LCD Commons, LCD Segment drivers, or CSD sense and shield pins can be connected to AMUXBUS A or B or can all be used as GPIO pins that can be driven by firmware or DSI signals.

The following package is supported: 28-pin SSOP.

Figure 3. 28-pin SSOP pinout



Development Support

The PSoC 4100 family has a rich set of documentation, development tools, and online resources to assist you during your development process. Visit www.cypress.com/go/psoc4 to find out more.

Documentation

A suite of documentation supports the PSoC 4100 family to ensure that you can find answers to your questions quickly. This section contains a list of some of the key documents.

Software User Guide: A step-by-step guide for using PSoC Creator. The software user guide shows you how the PSoC Creator build process works in detail, how to use source control with PSoC Creator, and much more.

Component Datasheets: The flexibility of PSoC allows the creation of new peripherals (components) long after the device has gone into production. Component data sheets provide all of the information needed to select and use a particular component, including a functional description, API documentation, example code, and AC/DC specifications.

Application Notes: PSoC application notes discuss a particular application of PSoC in depth; examples include brushless DC motor control and on-chip filtering. Application notes often include example projects in addition to the application note document.

Technical Reference Manual: The Technical Reference Manual (TRM) contains all the technical detail you need to use a PSoC device, including a complete description of all PSoC registers. The TRM is available in the Documentation section at www.cypress.com/psoc4.

Online

In addition to print documentation, the Cypress PSoC forums connect you with fellow PSoC users and experts in PSoC from around the world, 24 hours a day, 7 days a week.

Tools

With industry standard cores, programming, and debugging interfaces, the PSoC 4100 family is part of a development tool ecosystem. Visit us at www.cypress.com/go/psoccreator for the latest information on the revolutionary, easy to use PSoC Creator IDE, supported third party compilers, programmers, debuggers, and development kits.

Electrical Specifications

Absolute Maximum Ratings

Table 2. Absolute Maximum Ratings[1]

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID1	V_{DDD_ABS}	Digital supply relative to V_{SSD}	–0.5	–	6	V	Absolute max
SID2	V_{CCD_ABS}	Direct digital core voltage input relative to V_{SSD}	–0.5	–	1.95	V	Absolute max
SID3	V_{GPIO_ABS}	GPIO voltage	–0.5	–	V_{DD}+0.5	V	Absolute max
SID4	I_{GPIO_ABS}	Maximum current per GPIO	–25	–	25	mA	Absolute max
SID5	$I_{GPIO\_injection}$	GPIO injection current, Max for $V_{IH} > V_{DDD}$, and Min for $V_{IL} < V_{SS}$	–0.5	–	0.5	mA	Absolute max, current injected per pin
BID44	ESD_HBM	Electrostatic discharge human body model	2200	–	–	V	
BID45	ESD_CDM	Electrostatic discharge charged device model	500	–	–	V	
BID46	LU	Pin current for latch-up	–200	–	200	mA	

Device-Level Specifications

All specifications are valid for –40 °C ≤ T_A ≤ 85 °C for A grade devices and -40 °C ≤ T_A ≤ 105 °C for S grade devices, except where noted. Specifications are valid for 1.71 V to 5.5 V, except where noted.

Table 3. DC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID53	V_{DD}	Power supply input voltage ($V_{DDA} = V_{DDD} = V_{DD}$)	1.8	–	5.5	V	With regulator enabled
SID255	V_{DDD}	Power supply input voltage unregulated	1.71	1.8	1.89	V	Internally unregulated Supply
SID54	V_{CCD}	Output voltage (for core logic)	–	1.8	–	V	
SID55	C_{EFC}	External regulator voltage bypass	1	1.3	1.6	µF	X5R ceramic or better
SID56	C_{EXC}	Power supply decoupling capacitor	–	1	–	µF	X5R ceramic or better
Active Mode, V_{DD} = 1.71 V to 5.5 V. Typical Values measured at V_{DD} = 3.3 V.							
SID9	I_{DD4}	Execute from Flash; CPU at 6 MHz	–	–	2.8	mA	
SID10	I_{DD5}	Execute from Flash; CPU at 6 MHz	–	2.2	–	mA	T = 25 °C
SID12	I_{DD7}	Execute from Flash; CPU at 12 MHz	–	–	4.2	mA	
SID13	I_{DD8}	Execute from Flash; CPU at 12 MHz	–	3.7	–	mA	T = 25 °C
SID16	I_{DD11}	Execute from Flash; CPU at 24 MHz	–	6.7	–	mA	T = 25 °C
SID17	I_{DD12}	Execute from Flash; CPU at 24 MHz	–	–	7.2	mA	

Note

1. Usage above the absolute maximum conditions listed in Table 2 may cause permanent damage to the device. Exposure to absolute maximum conditions for extended periods of time may affect device reliability. The maximum storage temperature is 150 °C in compliance with JEDEC Standard JESD22-A103, High Temperature Storage Life. When used below absolute maximum conditions but above normal operating conditions, the device may not operate to specification.

GPIO

Table 4. GPIO DC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID57	V_{IH}[2]	Input voltage high threshold	0.7 × V_{DDD}	–	–	V	CMOS Input
SID58	V_{IL}	Input voltage low threshold	–	–	0.3 × V_{DDD}	V	CMOS Input
SID241	V_{IH}[2]	LVTTL input, V_{DDD} < 2.7 V	0.7× V_{DDD}	–	–	V	
SID242	V_{IL}	LVTTL input, V_{DDD} < 2.7 V	–	–	0.3 × V_{DDD}	V	
SID243	V_{IH}[2]	LVTTL input, $V_{DDD} \geq$ 2.7 V	2.0	–	–	V	
SID244	V_{IL}	LVTTL input, $V_{DDD} \geq$ 2.7 V	–	–	0.8	V	
SID59	V_{OH}	Output voltage high level	V_{DDD} –0.6	–	–	V	I_{OH} = 4 mA at 3 V V_{DDD}
SID60	V_{OH}	Output voltage high level	V_{DDD} –0.5	–	–	V	I_{OH} = 1 mA at 1.8 V V_{DDD}
SID61	V_{OL}	Output voltage low level	–	–	0.6	V	I_{OL} = 4 mA at 1.8 V V_{DDD}
SID62	V_{OL}	Output voltage low level	–	–	0.6	V	I_{OL} = 8 mA at 3 V V_{DDD}
SID62A	V_{OL}	Output voltage low level	–	–	0.4	V	I_{OL} = 3 mA at 3 V V_{DDD}
SID63	R_{PULLUP}	Pull-up resistor	3.5	5.6	8.5	kΩ	
SID64	$R_{PULLDOWN}$	Pull-down resistor	3.5	5.6	8.5	kΩ	
SID65	I_{IL}	Input leakage current (absolute value)	–	–	2	nA	25 °C, V_{DDD} = 3.0 V
SID65A	I_{IL_CTBM}	Input leakage current (absolute value) for CTBM pins	–	–	4	nA	
SID66	C_{IN}	Input capacitance	–	–	7	pF	
SID67	V_{HYSTTL}	Input hysteresis LVTTL	25	40	–	mV	$V_{DDD} \geq$ 2.7 V. Guaranteed by characterization
SID68	$V_{HYSCMOS}$	Input hysteresis CMOS	0.05 × V_{DDD}	–	–	mV	Guaranteed by characterization
SID69	I_{DIODE}	Current through protection diode to V_{DD}/Vss	–	–	100	µA	Guaranteed by characterization
SID69A	I_{TOT_GPIO}	Maximum total source or sink chip current	–	–	200	mA	Guaranteed by characterization

Note
2. V_{IH} must not exceed V_{DDD} + 0.2 V.

Analog Peripherals

Opamp

Table 8. Opamp Specifications (Guaranteed by Characterization)

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
	I_{DD}	Opamp block current. No load.	–	–	–	–	
SID269	I_{DD_HI}	Power = high	–	1100	1850	µA	
SID270	I_{DD_MED}	Power = medium	–	550	950	µA	
SID271	I_{DD_LOW}	Power = low	–	150	350	µA	
	GBW	Load = 20 pF, 0.1 mA. V_{DDA} = 2.7 V	–	–	–	–	
SID272	GBW_HI	Power = high	6	–	–	MHz	
SID273	GBW_MED	Power = medium	4	–	–	MHz	
SID274	GBW_LO	Power = low	–	1	–	MHz	
	I_{OUT_MAX}	$V_{DDA} \geq$ 2.7 V, 500 mV from rail	–	–	–	–	
SID275	$I_{OUT\_MAX\_HI}$	Power = high	10	–	–	mA	
SID276	$I_{OUT\_MAX\_MID}$	Power = medium	10	–	–	mA	
SID277	$I_{OUT\_MAX\_LO}$	Power = low	–	5	–	mA	
	I_{OUT}	V_{DDA} = 1.71 V, 500 mV from rail	–	–	–	–	
SID278	$I_{OUT\_MAX\_HI}$	Power = high	4	–	–	mA	
SID279	$I_{OUT\_MAX\_MID}$	Power = medium	4	–	–	mA	
SID280	$I_{OUT\_MAX\_LO}$	Power = low	–	2	–	mA	
SID281	V_{IN}	Charge pump on, $V_{DDA} \geq$ 2.7 V	–0.05	–	V_{DDA} – 0.2	V	
SID282	V_{CM}	Charge pump on, $V_{DDA} \geq$ 2.7 V	–0.05	–	V_{DDA} – 0.2	V	
	V_{OUT}	$V_{DDA} \geq$ 2.7 V	–	–	–		
SID283	V_{OUT_1}	Power = high, Iload=10 mA	0.5	–	V_{DDA} – 0.5	V	
SID284	V_{OUT_2}	Power = high, Iload=1 mA	0.2	–	V_{DDA} – 0.2	V	
SID285	V_{OUT_3}	Power = medium, Iload=1 mA	0.2	–	V_{DDA} – 0.2	V	
SID286	V_{OUT_4}	Power = low, Iload=0.1mA	0.2	–	V_{DDA} – 0.2	V	
SID288	V_{OS_TR}	Offset voltage, trimmed	1	±0.5	1	mV	High mode
SID288A	V_{OS_TR}	Offset voltage, trimmed	–	±1	–	mV	Medium mode
SID288B	V_{OS_TR}	Offset voltage, trimmed	–	±2	–	mV	Low mode
SID290	$V_{OS\_DR\_TR}$	Offset voltage drift, trimmed	–10	±3	10	µV/°C	High mode $T_A \leq$ 85 °C.
SID290Q	$V_{OS\_DR\_TR}$	Offset voltage drift, trimmed	–15	±3	15	µV/°C	High mode. $T_A \leq$ 105 °C
SID290A	$V_{OS\_DR\_TR}$	Offset voltage drift, trimmed	–	±10	–	µV/°C	Medium mode
SID290B	$V_{OS\_DR\_TR}$	Offset voltage drift, trimmed	–	±10	–	µV/°C	Low mode
SID291	CMRR	DC	70	80	–	dB	V_{DDD} = 3.6 V
SID292	PSRR	At 1 kHz, 100 mV ripple	70	85	–	dB	V_{DDD} = 3.6 V
	Noise		–	–	–	–	
SID293	V_{N1}	Input referred, 1 Hz - 1GHz, power = high	–	94	–	µVrms	
SID294	V_{N2}	Input referred, 1 kHz, power = high	–	72	–	nV/rtHz	
SID295	V_{N3}	Input referred, 10 kHz, power = high	–	28	–	nV/rtHz	
SID296	V_{N4}	Input referred, 100 kHz, power = high	–	15	–	nV/rtHz	

Table 8. Opamp Specifications (Guaranteed by Characterization) *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID297	Cload	Stable up to maximum load. Performance specs at 50 pF.	–	–	125	pF	
SID298	Slew_rate	Cload = 50 pF, Power = High, V_{DDA} ≥ 2.7 V	6	–	–	V/µs	
SID299	T_op_wake	From disable to enable, no external RC dominating	–	300	–	µs	
	Comp_mode	Comparator mode; 50 mV drive, Trise = Tfall (approx.)	–	–	–		
SID299A	OL_GAIN	Open Loop Gain	–	90	–	dB	Guaranteed by design
SID300	T_{PD1}	Response time; power = high	–	150	–	ns	
SID301	T_{PD2}	Response time; power = medium	–	400	–	ns	
SID302	T_{PD3}	Response time; power = low	–	2000	–	ns	
SID303	Vhyst_op	Hysteresis	–	10	–	mV	

Comparator

Table 9. Comparator DC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID85	$V_{OFFSET2}$	Input offset voltage, Common Mode voltage range from 0 to V_{DD}-1	–	–	±4	mV	
SID85A	$V_{OFFSET3}$	Input offset voltage. Ultra low-power mode (V_{DDD} ≥ 2.2 V for Temp < 0 °C, V_{DDD} ≥ 1.8 V for Temp > 0 °C)	–	±12	–	mV	
SID86	V_{HYST}	Hysteresis when enabled, Common Mode voltage range from 0 to V_{DD} -1.	–	10	35	mV	Guaranteed by characterization
SID87	V_{ICM1}	Input common mode voltage in normal mode	0	–	V_{DDD} – 0.1	V	Modes 1 and 2
SID247	V_{ICM2}	Input common mode voltage in low power mode (V_{DDD} ≥ 2.2 V for Temp < 0 °C, V_{DDD} ≥ 1.8 V for Temp > 0 °C)	0	–	V_{DDD}	V	
SID247A	V_{ICM3}	Input common mode voltage in ultra low power mode	0	–	V_{DDD} – 1.15	V	
SID88	CMRR	Common mode rejection ratio	50	–	–	dB	V_{DDD} ≥ 2.7 V. Guaranteed by characterization
SID88A	CMRR	Common mode rejection ratio	42	–	–	dB	V_{DDD} < 2.7 V. Guaranteed by characterization
SID89	I_{CMP1}	Block current, normal mode	–	–	400	µA	Guaranteed by characterization
SID248	I_{CMP2}	Block current, low power mode	–	–	100	µA	Guaranteed by characterization
SID259	I_{CMP3}	Block current, ultra low power mode (V_{DDD} ≥ 2.2 V for Temp < 0 °C, V_{DDD} ≥ 1.8 V for Temp > 0 °C)	–	6	28	µA	Guaranteed by characterization
SID90	Z_{CMP}	DC input impedance of comparator	35	–	–	MΩ	Guaranteed by characterization

Table 10. Comparator AC Specifications

(Guaranteed by Characterization)

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID91	T_{RESP1}	Response time, normal mode	–	–	110	ns	50 mV overdrive
SID258	T_{RESP2}	Response time, low power mode	–	–	200	ns	50 mV overdrive
SID92	T_{RESP3}	Response time, ultra low power mode ($V_{DDD} \geq 2.2$ V for Temp < 0 °C, $V_{DDD} \geq 1.8$ V for Temp > 0 °C)	–	–	15	µs	200 mV overdrive

Temperature Sensor

Table 11. Temperature Sensor Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID93	$T_{SENSACC}$	Temperature sensor accuracy	–5	±1	+5	°C	–40 to +85 °C

SAR ADC

Table 12. SAR ADC DC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID94	A_RES	Resolution	–	–	12	bits	
SID95	A_CHNIS_S	Number of channels - single ended	–	–	8		8 full speed
SID96	A-CHNKS_D	Number of channels - differential	–	–	4		Diff inputs use neighboring I/O
SID97	A-MONO	Monotonicity	–	–	–		Yes. Based on characterization
SID98	A_GAINERR	Gain error	–	–	±0.1	%	With external reference. Guaranteed by characterization
SID99	A_OFFSET	Input offset voltage	–	–	2	mV	Measured with 1-V $V_{REF.}$ Guaranteed by characterization
SID100	A_ISAR	Current consumption	–	–	1	mA	
SID101	A_VINS	Input voltage range - single ended	V_{SS}	–	V_{DDA}	V	Based on device characterization
SID102	A_VIND	Input voltage range - differential	V_{SS}	–	V_{DDA}	V	Based on device characterization
SID103	A_INRES	Input resistance	–	–	2.2	KΩ	Based on device characterization
SID104	A_INCAP	Input capacitance	–	–	10	pF	Based on device characterization

Table 13. SAR ADC AC Specifications (Guaranteed by Characterization)

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID106	A_PSRR	Power supply rejection ratio	70	–	–	dB	
SID107	A_CMRR	Common mode rejection ratio	66	–	–	dB	Measured at 1 V
SID108	A_SAMP_1	Sample rate with external reference bypass cap	–	–	1	Msps	
SID108A	A_SAMP_2	Sample rate with no bypass cap. Reference = V_{DD}	–	–	806	Ksps	
SID108B	A_SAMP_3	Sample rate with no bypass cap. Internal reference	–	–	100	Ksps	
SID109	A_SNDR	Signal-to-noise and distortion ratio (SINAD)	65	–	–	dB	F_{IN} = 10 kHz
SID111	A_INL	Integral non linearity	–1.7	–	+2	LSB	V_{DD} = 1.71 to 5.5, 806 Ksps, Vref = 1 to 5.5. –40 °C ≤ T_A ≤ 85 °C
			–1.9	–	+2	LSB	V_{DD} = 1.71 to 5.5, 806 Ksps, Vref = 1 to 5.5. –40 °C ≤ T_A ≤ 105 °C
SID111A	A_INL	Integral non linearity	–1.5	–	+1.7	LSB	V_{DDD} = 1.71 to 3.6, 806 Ksps, Vref = 1.71 to V_{DDD}. –40 °C ≤ T_A ≤ 85 °C
			–1.9	–	+2	LSB	V_{DDD} = 1.71 to 3.6, 806 Ksps, Vref = 1.71 to V_{DDD}. –40 °C ≤ T_A ≤ 105 °C
SID111B	A_INL	Integral non linearity	–1.5	–	+1.7	LSB	V_{DDD} = 1.71 to 5.5, 500 Ksps, Vref = 1 to 5.5.
SID112	A_DNL	Differential non linearity	–1	–	+2.2	LSB	V_{DDD} = 1.71 to 5.5, 806 Ksps, Vref = 1 to 5.5. –40 °C ≤ T_A ≤ 85 °C
			–1	–	+2.3	LSB	V_{DDD} = 1.71 to 5.5, 806 Ksps, Vref = 1 to 5.5. –40 °C ≤ T_A ≤ 105 °C
SID112A	A_DNL	Differential non linearity	–1	–	+2	LSB	V_{DDD} = 1.71 to 3.6, 806 Ksps, Vref = 1.71 to V_{DDD}. –40 °C ≤ T_A ≤ 85 °C
			–1	–	+2.2	LSB	V_{DDD} = 1.71 to 3.6, 806 Ksps, Vref = 1.71 to V_{DDD}. –40 °C ≤ T_A ≤ 105 °C
SID112B	A_DNL	Differential non linearity	–1	–	+2.2	LSB	V_{DDD} = 1.71 to 5.5, 500 Ksps, Vref = 1 to 5.5.
SID113	A_THD	Total harmonic distortion	–	–	–65	dB	F_{IN} = 10 kHz.

Memory

Table 26. Flash DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID173	V_{PE}	Erase and program voltage	1.71	–	5.5	V	

Table 27. Flash AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID174	$T_{ROWWRITE}$[3]	Row (block) write time (erase and program)	–	–	20	ms	Row (block) = 128 bytes. –40 °C ≤ T_A ≤ 85 °C
			–	–	26	ms	Row (block) = 128 bytes. –40 °C ≤ T_A ≤ 105 °C
SID175	$T_{ROWERASE}$[3]	Row erase time	–	–	13	ms	
SID176	$T_{ROWPROGRAM}$[3]	Row program time after erase	–	–	7	ms	–40 °C ≤ T_A ≤ 85 °C
			–	–	13	ms	–40 °C ≤ T_A ≤ 105 °C
SID178	$T_{BULKERASE}$[3]	Bulk erase time (32 KB)	–	–	35	ms	
SID180	$T_{DEVPROG}$[3]	Total device program time	–	–	7	seconds	Guaranteed by characterization
SID181	F_{END}	Flash endurance	100 K	–	–	cycles	Guaranteed by characterization
SID182	F_{RET}	Flash retention. T_A ≤ 55 °C, 100 K P/E cycles	20	–	–	years	Guaranteed by characterization
SID182A		Flash retention. T_A ≤ 85 °C, 10 K P/E cycles	10	–	–	years	Guaranteed by characterization
SID182B	F_{RETQ}	Flash retention. T_A ≤ 105 °C, 10K P/E cycles, ≤ three years at T_A ≥ 85 °C.	10	20	–		Guaranteed by characterization.

System Resources

Power-on-Reset (POR) with Brown Out

Table 28. Imprecise Power On Reset (PRES)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID185	$V_{RISEIPOR}$	Rising trip voltage	0.80	–	1.45	V	Guaranteed by characterization
SID186	$V_{FALLIPOR}$	Falling trip voltage	0.75	–	1.4	V	Guaranteed by characterization
SID187	$V_{IPORHYST}$	Hysteresis	15	–	200	mV	Guaranteed by characterization

Table 29. Precise Power On Reset (POR)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID190	$V_{FALLPPOR}$	BOD trip voltage in active and sleep modes	1.64	–	–	V	Full functionality between 1.71 V and BOD trip voltage is guaranteed by characterization
SID192	$V_{FALLDPSLP}$	BOD trip voltage in Deep Sleep	1.4	–	–	V	Guaranteed by characterization
BID55	Svdd	Maximum power supply ramp rate	–	–	67	kV/sec	

Note
3. It can take as much as 20 milliseconds to write to Flash. During this time the device should not be Reset, or Flash operations will be interrupted and cannot be relied on to have completed. Reset sources include the XRES pin, software resets, CPU lockup states and privilege violations, improper power supply levels, and watchdogs. Make certain that these are not inadvertently activated.

Voltage Monitors

Table 30. Voltage Monitors DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID195	V_{LVI1}	LVI_A/D_SEL[3:0] = 0000b	1.71	1.75	1.79	V	
SID196	V_{LVI2}	LVI_A/D_SEL[3:0] = 0001b	1.76	1.80	1.85	V	
SID197	V_{LVI3}	LVI_A/D_SEL[3:0] = 0010b	1.85	1.90	1.95	V	
SID198	V_{LVI4}	LVI_A/D_SEL[3:0] = 0011b	1.95	2.00	2.05	V	
SID199	V_{LVI5}	LVI_A/D_SEL[3:0] = 0100b	2.05	2.10	2.15	V	
SID200	V_{LVI6}	LVI_A/D_SEL[3:0] = 0101b	2.15	2.20	2.26	V	
SID201	V_{LVI7}	LVI_A/D_SEL[3:0] = 0110b	2.24	2.30	2.36	V	
SID202	V_{LVI8}	LVI_A/D_SEL[3:0] = 0111b	2.34	2.40	2.46	V	
SID203	V_{LVI9}	LVI_A/D_SEL[3:0] = 1000b	2.44	2.50	2.56	V	
SID204	V_{LVI10}	LVI_A/D_SEL[3:0] = 1001b	2.54	2.60	2.67	V	
SID205	V_{LVI11}	LVI_A/D_SEL[3:0] = 1010b	2.63	2.70	2.77	V	
SID206	V_{LVI12}	LVI_A/D_SEL[3:0] = 1011b	2.73	2.80	2.87	V	
SID207	V_{LVI13}	LVI_A/D_SEL[3:0] = 1100b	2.83	2.90	2.97	V	
SID208	V_{LVI14}	LVI_A/D_SEL[3:0] = 1101b	2.93	3.00	3.08	V	
SID209	V_{LVI15}	LVI_A/D_SEL[3:0] = 1110b	3.12	3.20	3.28	V	
SID210	V_{LVI16}	LVI_A/D_SEL[3:0] = 1111b	4.39	4.50	4.61	V	
SID211	LVI_IDD	Block current	–	–	100	µA	Guaranteed by characterization

Table 31. Voltage Monitors AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID212	$T_{MONTRIP}$	Voltage monitor trip time	–	–	1	µs	Guaranteed by characterization

SWD Interface

Table 32. SWD Interface Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID213	F_SWDCLK1	$3.3\ V \le V_{DD} \le 5.5\ V$	–	–	14	MHz	SWDCLK ≤ 1/3 CPU clock frequency
SID214	F_SWDCLK2	$1.71\ V \le V_{DD} \le 3.3\ V$	–	–	7	MHz	SWDCLK ≤ 1/3 CPU clock frequency
SID215	T_SWDI_SETUP	T = 1/f SWDCLK	0.25*T	–	–	ns	Guaranteed by characterization
SID216	T_SWDI_HOLD	T = 1/f SWDCLK	0.25*T	–	–	ns	Guaranteed by characterization
SID217	T_SWDO_VALID	T = 1/f SWDCLK	–	–	0.5*T	ns	Guaranteed by characterization
SID217A	T_SWDO_HOLD	T = 1/f SWDCLK	1	–	–	ns	Guaranteed by characterization

Internal Main Oscillator

Table 33. IMO DC Specifications (Guaranteed by Design)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID219	I_{IMO2}	IMO operating current at 24 MHz	–	–	325	µA	
SID220	I_{IMO3}	IMO operating current at 12 MHz	–	–	225	µA	
SID221	I_{IMO4}	IMO operating current at 6 MHz	–	–	180	µA	
SID222	I_{IMO5}	IMO operating current at 3 MHz	–	–	150	µA	

Table 34. IMO AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID223	$F_{IMOTOL1}$	Frequency variation from 3 to 24 MHz	–	–	±2	%	±3% if T_A > 85 °C and IMO frequency < 24 MHz
SID226	$T_{STARTIMO}$	IMO startup time	–	–	12	µs	
SID227	$T_{JITRMSIMO1}$	RMS Jitter at 3 MHz	–	156	–	ps	
SID228	$T_{JITRMSIMO2}$	RMS Jitter at 24 MHz	–	145	–	ps	

Internal Low-Speed Oscillator

Table 35. ILO DC Specifications (Guaranteed by Design)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID231	I_{ILO1}	ILO operating current at 32 kHz	–	0.3	1.05	µA	Guaranteed by Characterization
SID233	$I_{ILOLEAK}$	ILO leakage current	–	2	15	nA	Guaranteed by Design

Table 36. ILO AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID234	$T_{STARTILO1}$	ILO startup time	–	–	2	ms	Guaranteed by characterization
SID236	$T_{ILODUTY}$	ILO duty cycle	40	50	60	%	Guaranteed by characterization
SID237	$F_{ILOTRIM1}$	32 kHz trimmed frequency	15	32	50	kHz	Max. ILO frequency is 70 kHz if T_A > 85 °C

Table 37. External Clock Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID305	ExtClkFreq	External Clock input Frequency	0	–	24	MHz	Guaranteed by characterization
SID306	ExtClkDuty	Duty cycle; Measured at $V_{DD/2}$	45	–	55	%	Guaranteed by characterization

Table 38. Block Specs

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID257	T_{WS24}*	Number of wait states at 24 MHz	0	–	–		CPU execution from Flash. Guaranteed by characterization
SID260	V_{REFSAR}	Trimmed internal reference to SAR	–1	–	+1	%	Percentage of Vbg (1.024 V). Guaranteed by characterization
SID262	$T_{CLKSWITCH}$	Clock switching from clk1 to clk2 in clk1 periods	3	–	4	Periods	Guaranteed by design

* Tws24 is guaranteed by design.

Ordering Information

The PSoC 4100 part numbers and features are listed in the Table 39.

Table 39. PSoC 4100 Family Ordering Information

Family	MPN	Features												Package	Operating Temperature	
		Max CPU Speed (MHz)	Flash (KB)	SRAM (KB)	UDB	Opamp (CTBm)	CapSense	Direct LCD Drive	12-bit SAR ADC	LP Comparators	TCPWM Blocks	SCB Blocks	GPIO	28-SSOP	–40 to +85 °C	–40 to +105 °C
4100	CY8C4124PVA-442Z	24	16	4	–	1	✔	✔	806 Ksps	2	4	2	24	✔	✔	–
	CY8C4125PVA-482Z	24	32	4	–	1	✔	✔	806 Ksps	2	4	2	24	✔	✔	–
	CY8C4124PVS-442Z	24	16	4	–	1	✔	✔	806 Ksps	2	4	2	24	✔	–	✔
	CY8C4125PVS-482Z	24	32	4	–	1	✔	✔	806 Ksps	2	4	2	24	✔	–	✔

Part Numbering Conventions

PSoC 4 devices follow the part numbering convention described in the following table. All fields are single-character alphanumeric (0, 1, 2, …, 9, A,B, …, Z) unless stated otherwise.

The part numbers are of the form CY8C4ABCDEF-GHI where the fields are defined as follows.

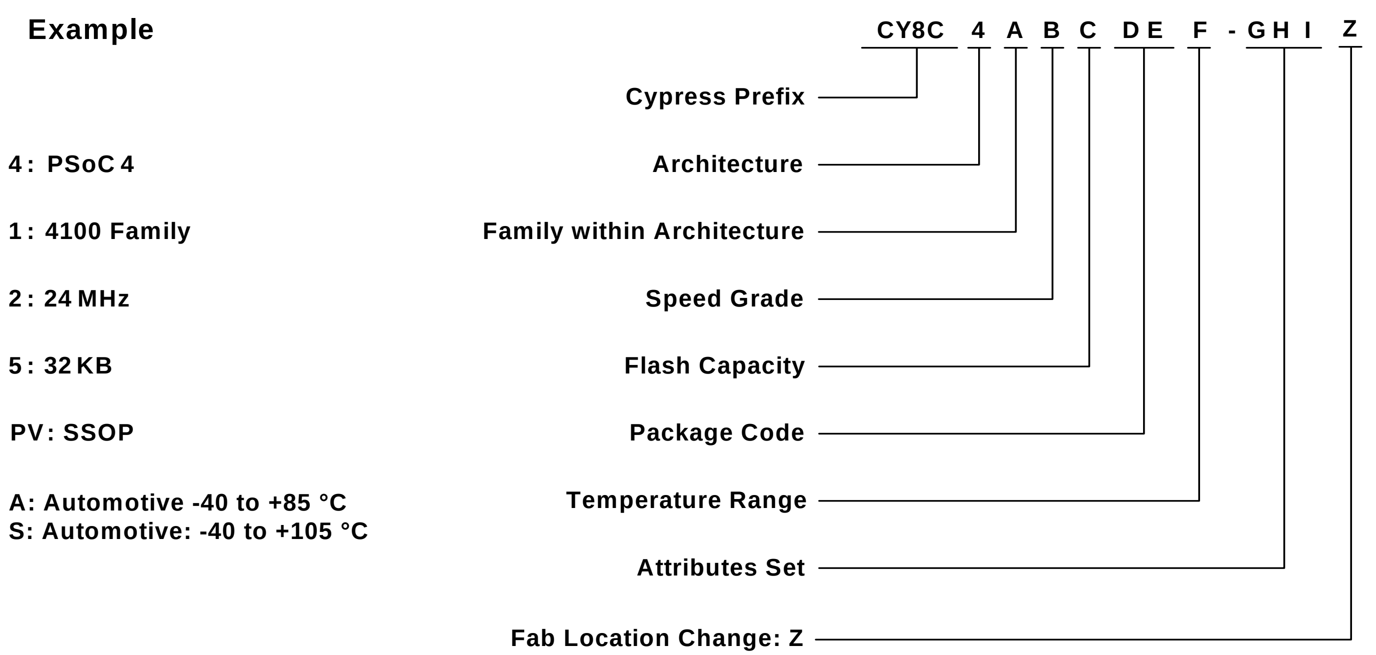


Figure 6. 28-pin SSOP (210 Mils) Package Outline

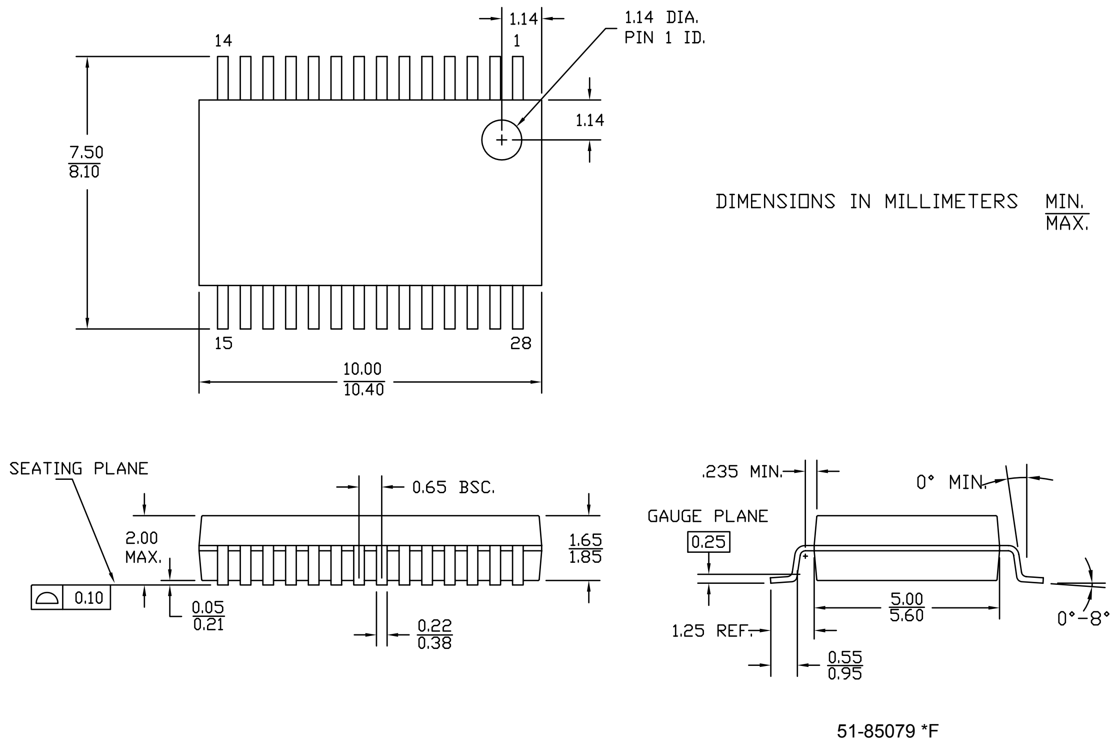


Table 44. Acronyms Used in this Document *(continued)*

Acronym	Description
PGA	programmable gain amplifier
PHUB	peripheral hub
PHY	physical layer
PICU	port interrupt control unit
PLA	programmable logic array
PLD	programmable logic device, see also PAL
PLL	phase-locked loop
PMDD	package material declaration data sheet
POR	power-on reset
PRES	precise power-on reset
PRS	pseudo random sequence
PS	port read data register
PSoC®	Programmable System-on-Chip™
PSRR	power supply rejection ratio
PWM	pulse-width modulator
RAM	random-access memory
RISC	reduced-instruction-set computing
RMS	root-mean-square
RTC	real-time clock
RTL	register transfer language
RTR	remote transmission request
RX	receive
SAR	successive approximation register
SC/CT	switched capacitor/continuous time
SCL	I^2C serial clock
SDA	I^2C serial data
S/H	sample and hold
SINAD	signal to noise and distortion ratio
SIO	special input/output, GPIO with advanced features. See GPIO.
SOC	start of conversion
SOF	start of frame
SPI	Serial Peripheral Interface, a communications protocol
SR	slew rate
SRAM	static random access memory
SRES	software reset
SWD	serial wire debug, a test protocol
SWV	single-wire viewer
TD	transaction descriptor, see also DMA

Table 44. Acronyms Used in this Document *(continued)*

Acronym	Description
THD	total harmonic distortion
TIA	transimpedance amplifier
TRM	technical reference manual
TTL	transistor-transistor logic
TX	transmit
UART	Universal Asynchronous Transmitter Receiver, a communications protocol
UDB	universal digital block
USB	Universal Serial Bus
USBIO	USB input/output, PSoC pins used to connect to a USB port
VDAC	voltage DAC, see also DAC, IDAC
WDT	watchdog timer
WOL	write once latch, see also NVL
WRES	watchdog timer reset
XRES	external reset I/O pin
XTAL	crystal

Document Conventions

Units of Measure

Table 45. Units of Measure

Symbol	Unit of Measure
°C	degrees Celsius
dB	decibel
fF	femto farad
Hz	hertz
KB	1024 bytes
kbps	kilobits per second
Khr	kilohour
kHz	kilohertz
kΩ	kilo ohm
Ksps	kilosamples per second
LSB	least significant bit
Mbps	megabits per second
MHz	megahertz
MΩ	mega-ohm
Msps	megasamples per second
µA	microampere
µF	microfarad
µH	microhenry
µs	microsecond
µV	microvolt
µW	microwatt
mA	milliampere
ms	millisecond
mV	millivolt
nA	nanoampere
ns	nanosecond
nV	nanovolt
Ω	ohm
pF	picofarad
ppm	parts per million
ps	picosecond
s	second
sps	samples per second
sqrtHz	square root of hertz
V	volt

Document History Page *(continued)*

Document Title: Automotive PSoC® 4: PSoC 4100 Family Datasheet Programmable System-on-Chip (PSoC®) Document Number: 001-93576				
Revision	ECN	Orig. of Change	Submission Date	Description of Change
*D (cont.)	5331416	MVRE	07/04/2016	Updated Electrical Specifications: Updated System Resources: Updated Power-on-Reset (POR) with Brown Out: Updated Table 29: Updated details in “Details/Conditions” column corresponding to $V_{FALLPPOR}$ parameter. Added Svdd parameter and its details. Updated Internal Main Oscillator: Updated Table 34: Updated details in “Details/Conditions” column corresponding to $F_{IMOTOL1}$ parameter. Updated Internal Low-Speed Oscillator: Updated Table 36: Updated details in “Details/Conditions” column corresponding to $F_{ILOTRIM1}$ parameter. Updated Packaging: Updated description. Updated to new template. Completing Sunset Review.
*E	5675099	SNPR	03/28/2017	Updated Ordering Information.